

HALOGEN

FREE



Quad SPST CMOS Analog Switches

DESCRIPTION

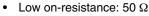
The DG441, DG442 monolithic quad analog switches are designed to provide high speed, low error switching of analog and audio signals. The DG441 has a normally closed function. The DG442 has a normally open function. Combining low on-resistance (50 Ω , typ.) with high speed (toN 150 ns, typ.), the DG441, DG442 are ideally suited for upgrading DG201A/202 sockets. Charge injection has been minimized on the drain for use in sample-and-hold circuits.

To achieve high voltage ratings and superior switching performance, the DG441, DG442 are built on Vishay Siliconix's high-voltage silicon-gate process. An epitaxial layer prevents latchup.

Each switch conducts equally well in both directions when on, and blocks input voltages to the supply levels when off.

FEATURES

 Halogen-free according to IEC 61249-2-21 Definition



· Low leakage: 80 pA

Low power consumption: 0.2 mW

• Fast switching action - t_{ON}: 150 ns

• Low charge injection - Q: - 1 pC

• DG201A/DG202 upgrades

TTL/CMOS-compatible logic

Single supply capability

Compliant to RoHS Directive 2002/95/EC

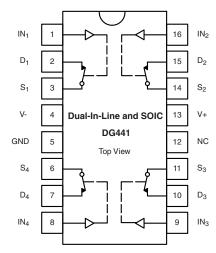
BENEFITS

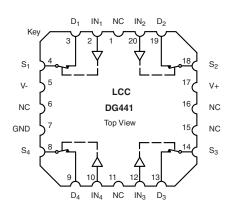
- Less signal errors and distortion
- Reduced power supply requirements
- Faster throughput
- Improved reliability
- · Reduced pedestal errors
- · Simplifies retrofit
- Simple interfacing

APPLICATIONS

- Audio switching
- Battery powered systems
- Data acquisition
- · Hi-Rel systems
- · Sample-and-hold circuits
- Communication systems
- Automatic test equipment
- Medical instruments

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION





TRUTH TABLE						
Logic	DG441	DG442				
0	On	Off				
1	Off	On				

Logic "0" \leq 0.8 V Logic "1" \geq 2.4 V

Document Number: 70053 S11-1066-Rev. J, 30-May-11

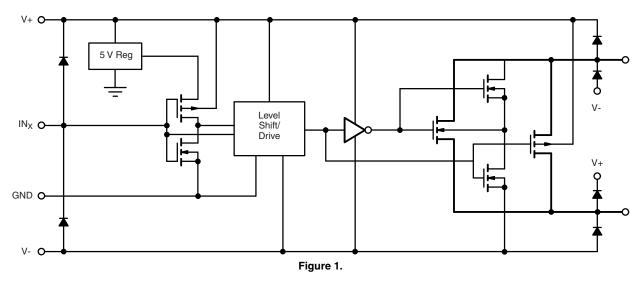


ORDERING INFORMATION					
Temp. Range	Package	Part Number			
- 40 °C to 85 °C	16-pin plastic DIP	DG441DJ DG441DJ-E3			
	то-ріп ріазііс діг	DG442DJ DG442DJ-E3			
	16 pip payrow SOIC	DG441DY DG441DY-E3 DG441DY-T1 DG441DY-T1-E3			
	16-pin narrow SOIC	DG442DY DG442DY-E3 DG442DY-T1 DG442DY-T1-E3			

Parameter		Limit	Unit		
V+ to V-		44			
GND to V-		25	V		
Digital Inputs ^a , V _S , V _D		(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first			
Continuous Current (any terminal)		30	mA		
Current, S or D (pulsed at 1 ms, 10 % duty cycle)		100	IIIA		
Storage Temperature	(AK suffix)	- 65 to 150	°C		
Storage Temperature	(DJ, DY suffix)	- 65 to 125			
	16-pin plastic DIP ^c	450			
Power Dissipation (Package) ^b	16-pin CerDIP ^d	900	mW		
	16-pin narrow SOIC ^d	900			
	LCC-20 ^d	1200			

- a. Signals on S_X , D_X , or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 6 mW/°C above 75 °C.
- d. Derate 12 mW/°C above 75 °C.

SCHEMATIC DIAGRAM Typical Channel





SPECIFICATIO	NS ^a (Du	ual Supplie	es)							
	·	•	Test Conditions Unless Otherwise Specified V+ = 15 V, V- = - 15 V			_	uffix o 125 °C	_	uffix to 85 °C	
Parameter		Symbol	$V_{IN} = 2.4 \text{ V}, 0.8 \text{ V}^{f}$	Temp.b	Typ. ^c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	Unit
Analog Switch		-	<u></u>				•			ı
Analog Signal Range ^e		V _{ANALOG}		Full		- 15	15	- 15	15	V
Drain-Source On-Resistance		R _{DS(on)}	I _S = - 10 mA, V _D = ± 8.5 V V+ = 13.5 V, V- = - 13.5 V	Room Full	50		85 100		85 100	Ω
On-Resistance Match I Channels ^e	Between	$\Delta R_{DS(on)}$	$I_S = -10 \text{ mA}, V_D = \pm 10 \text{ V}$ V+ = 15 V, V- = -15 V	Room Full			4 5		4 5	52
Switch Off Leakage Cu	ırrent	I _{S(off)}	V+ = 16.5, V- = - 16.5 V	Room Full	± 0.01	- 0.5 - 20	0.5 20	- 0.5 - 5	0.5 5	
Owner on Leakage of	mont	I _{D(off)}	$V_D = \pm 15.5 \text{ V}, V_S = \pm 15.5 \text{ V}$	Room Full	± 0.01	- 0.5 - 20	0.5 20	- 0.5 - 5	0.5 5	nA
Channel On Leakage (Current	$I_{D(on)}$	V+ = 16.5 V, V- = -16.5 V $V_S = V_D = \pm 15.5 \text{ V}$	Room Full	± 0.08	- 0.5 - 40	0.5 40	- 0.5 - 10	0.5 10	
Digital Control										
Input Current V _{IN} Low		I _{IL}	V _{IN} under test = 0.8 V, All Other = 2.4 V	Full	- 0.01	- 500	500	- 500	500	nA
Input Current V _{IN} High		I _{IH}	V _{IN} under test = 2.4 V All Other = 0.8 V	Full	0.01	- 500	500	- 500	500	IIA
Dynamic Characteris	tics									
Turn-On Time		t _{ON}	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}$	Room	150		250		250	
Turn-Off Time	DG441	t _{OFF}	$V_{S} = \pm 10 \text{ V}$	Room	90		120		120	ns
	DG442	011	See Figure 2	Room	110		210		210	
Charge Injection ^e		Q	$C_L = 1 \text{ nF, } V_S = 0 \text{ V}$ $V_{gen} = 0 \text{ V, } R_{gen} = 0 \Omega$	Room	- 1					рС
Off Isolation ^e		OIRR	$R_1 = 50 \Omega$, $C_1 = 5 pF$	Room	60					
Crosstalk (Channel-to- Channel)		X _{TALK}	f = 1 MHz	Room	100					dB
Source Off Capacitance ^e		C _{S(off)}	f = 1 MHz	Room	4					
Drain Off Capacitance ^e		C _{D(off)}	1 – 1 1011 12	Room	4					pF
Channel On Capacitance ^e		C _{D(on)}	V _{ANALOG} = 0 V	Room	16					
Power Supplies										
Positive Supply Curren	t	l+		Full	15		100		100	
Negative Supply Current		l-	V+ = 16.5 V, V- = - 16.5 V V _{IN} = 0 or 5 V	Room Full	- 0.0001	- 1 - 5		- 1 - 5		μΑ
Ground Current		I _{GND}		Full	- 15	- 100		- 100		



SPECIFICATIONS ^a (Single Supply)									
		Test Conditions Unless Otherwise Specified			_	uffix o 125 °C	_	uffix to 85 °C	
Parameter	Symbol	V+ = 12 V, V- = 0 V $V_{IN} = 2.4 V, 0.8 V^f$	Temp.b	Typ. ^c	Min. ^d	Max. ^d	Min. ^d	Max. ^d	Unit
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full		0	12	0	12	V
Drain-Source On-Resistance	R _{DS(on)}	$I_S = -10 \text{ mA}, V_D = 3 \text{ V}, 8 \text{ V}$ V+ = 10.8 V	Room Full	100		160 200		160 200	Ω
Dynamic Characteristics	Dynamic Characteristics								
Turn-On Time	t _{ON}	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}$	Room	300		450		450	
Turn-Off Time	t _{OFF}	V _S = 8 V See Figure 2	Room	60		200		200	ns
Charge Injection	Q	$C_L = 1nF, V_{gen} = 6 V, R_{gen} = 0 \Omega$	Room	2					рС
Power Supplies									
Positive Supply Current	l+		Full	15		100		100	
Negative Supply Current	l-	V+ = 13.2 V, V- = 0 V V _{IN} = 0 or 5 V	Room Full	- 0.0001	- 1 - 100		- 1 - 100		μΑ
Ground Current	I _{GND}		Full	- 15	- 100		- 100		

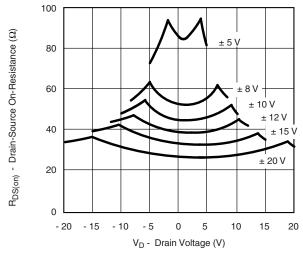
Notes:

- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25 $^{\circ}$ C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.

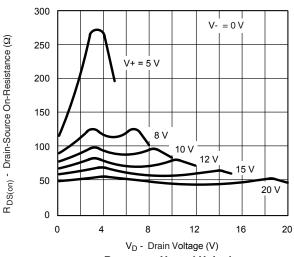
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



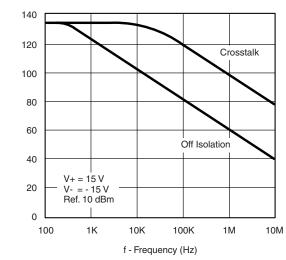
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



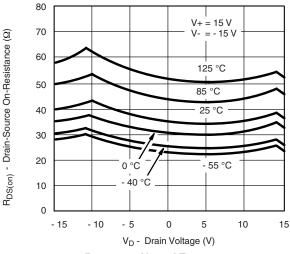
 $R_{DS(on)}$ vs. V_D and Power Supply Voltage



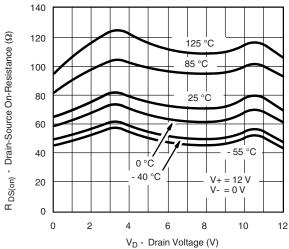
R_{DS(on)} vs. V_D and Unipolar **Power Supply Voltage**



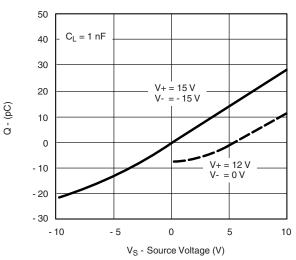
Crosstalk and Off Isolation vs. Frequency



 $R_{DS(on)}$ vs. V_D and Temperature

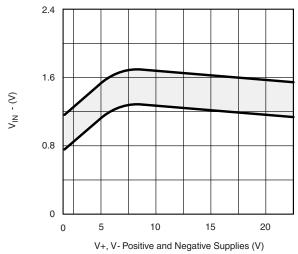


 $R_{DS(on)}\, vs. \, V_D$ and Temperature (Single 12-V Supply)

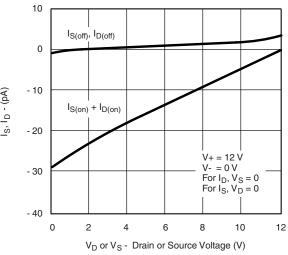


Charge Injection vs. Source Voltage

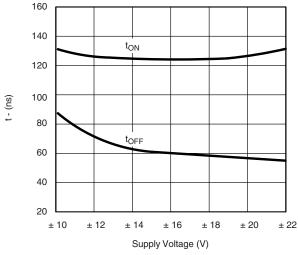
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



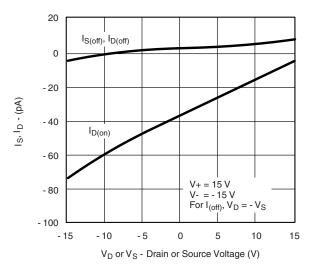
Switching Threshold vs. Supply Voltage



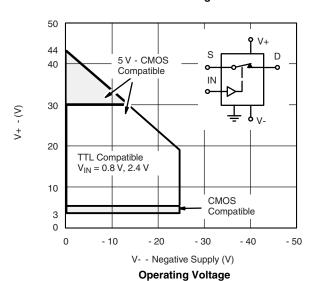
Source/Drain Leakage Currents (Single 12 V Supply)



Switching Time vs. Power Supply Voltage



Source/Drain Leakage Currents



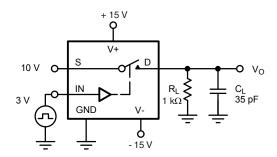
500 V- = 0 V400 t_{ON} 300 200 100 toff 8 10 14 16 18 20 22 V_S - Source Voltage (V)

Switching Time vs. Power Supply Voltage

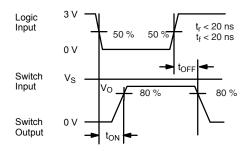




TEST CIRCUITS

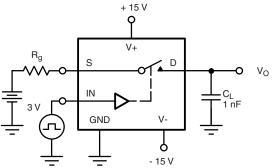


C_L (includes fixture and stray capacitance)



Logic input waveform is inverted for DG442.

Figure 2. Switching Time



ON OFF (DG441) ON OFF INx $Q = \Delta V_O \times C_L$ (DG442)

Figure 3. Charge Injection

C = 1 mF tantalum in parallel with 0.01 mF ceramic + 15 V D_1 0 V, 2.4 V O GND X_{TALK} Isolation = 20 log C = RF bypass

Figure 4. Crosstalk

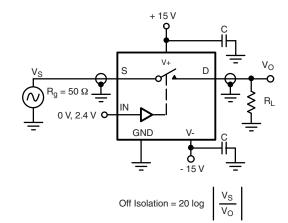


Figure 5. Off Isolation

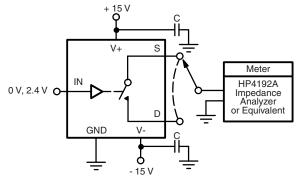


Figure 6. Source/Drain Capacitances

APPLICATIONS

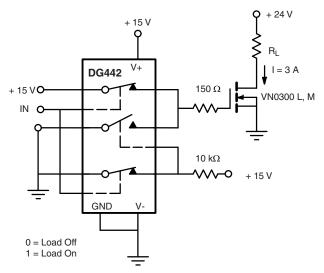


Figure 7. Power MOSFET Driver

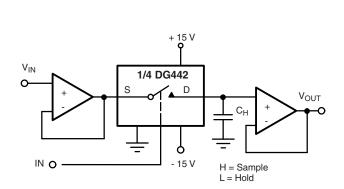


Figure 8. Open Loop Sample-and-Hold

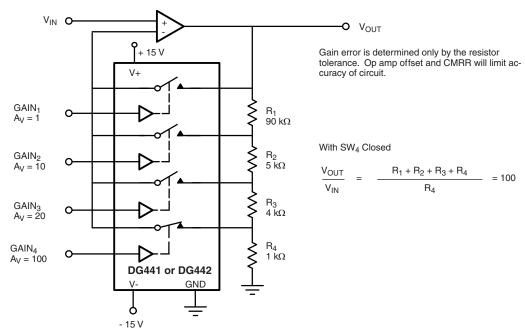
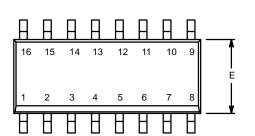


Figure 9. Precision-Weighted Resistor Programmable-Gain Amplifier

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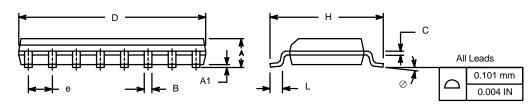
SOIC (NARROW): 16-LEAD
JEDEC Part Number: MS-012



	MILLIMETERS		INC	HES	
Dim	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.38	0.51	0.015	0.020	
С	0.18	0.23	0.007	0.009	
D	9.80	10.00	0.385	0.393	
E	3.80	4.00	0.149	0.157	
е	e 1.27 BSC 0.050 BSC				
Н	5.80	6.20	0.228	0.244	
L	0.50	0.93	0.020	0.037	
0	0°	8°	0°	8°	
ECN: S-03946—Rev E 09- Jul-01					

ECN: S-03946—Rev. F, 09-Jul-01

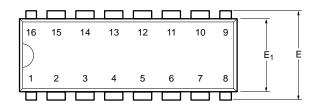
DWG: 5300

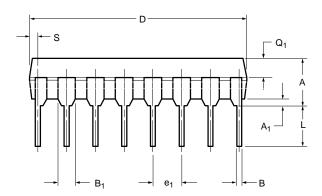


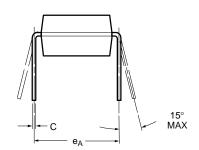
Document Number: 71194 www.vishay.com 02-Jul-01 sww.vishay.com



PDIP: 16-LEAD





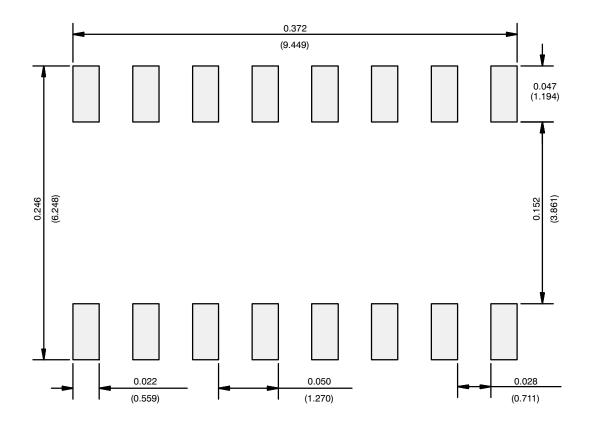


	MILLIM	IETERS	INC	HES	
Dim	Min	Max	Min	Max	
Α	3.81	5.08	0.150	0.200	
A ₁	0.38	1.27	0.015	0.050	
В	0.38	0.51	0.015	0.020	
B ₁	0.89	1.65	0.035	0.065	
С	0.20	0.30	0.008	0.012	
D	18.93	21.33	0.745	0.840	
Е	7.62	8.26	0.300	0.325	
E ₁	5.59	7.11	0.220	0.280	
e ₁	2.29	2.79	0.090	0.110	
e _A	7.37	7.87	0.290	0.310	
L	2.79	3.81	0.110	0.150	
Q_1	1.27	2.03	0.050	0.080	
S	0.38	1.52	.015	0.060	
ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5482					

Document Number: 71261 www.vishay.com 06-Jul-01 www.vishay.com



RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

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Vishay

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